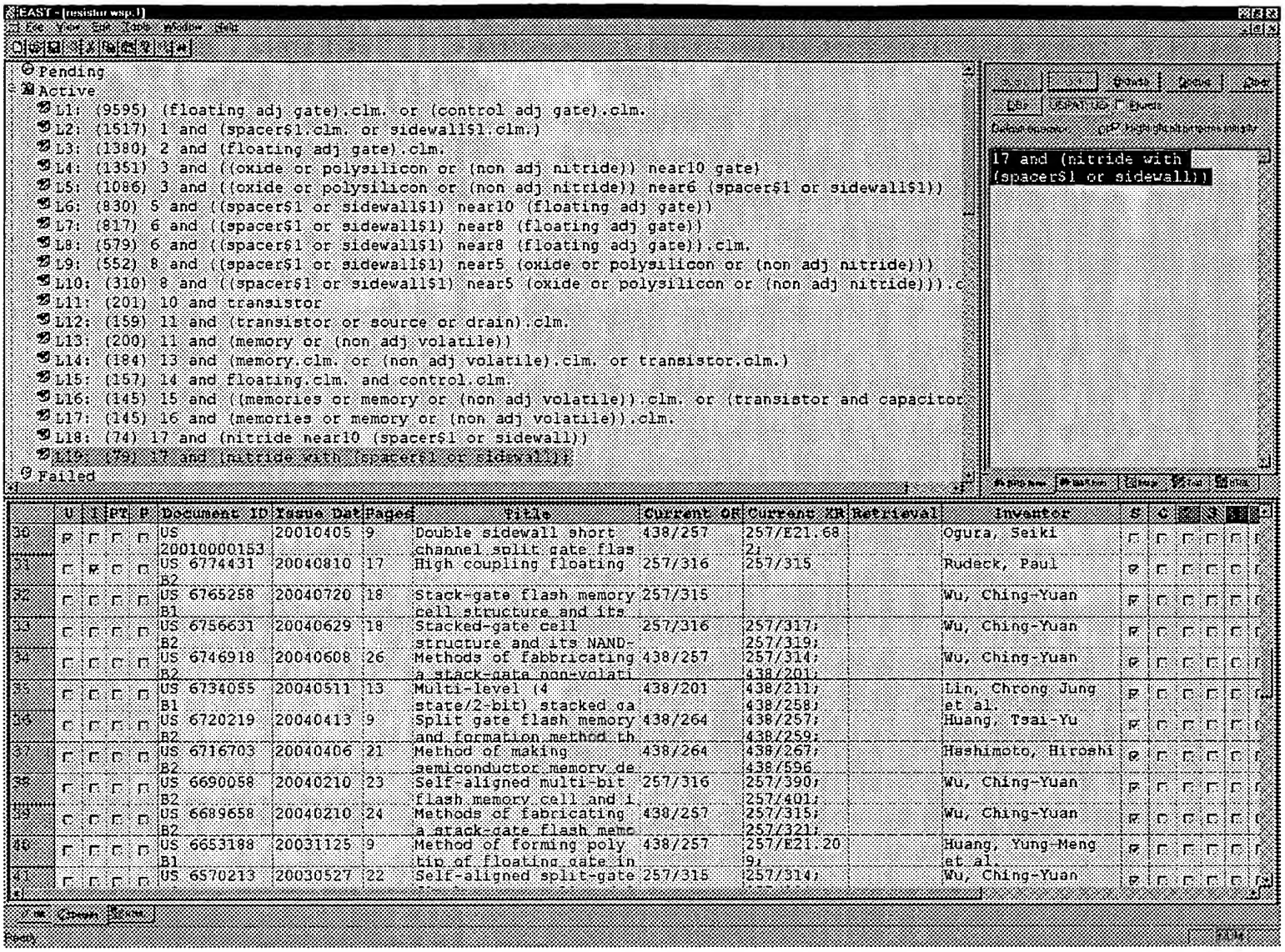

	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S
30	☐	☐	☐	☐	US 20010000153	20010405	9	Double sidewall short channel split gate flas	438/257	257/E21.68 2;		Ogura, Seiki	☐
31	☐	☒	☐	☐	US 6774431 B2	20040810	17	High coupling floating	257/316	257/315		Rudeck, Paul	☒
32	☐	☐	☐	☐	US 6765258 B1	20040720	18	Stack-gate flash memory cell structure and its	257/315			Wu, Ching-Yuan	☒
33	☐	☐	☐	☐	US 6756631 B2	20040629	18	Stacked-gate cell structure and its NAND-	257/316	257/317; 257/319;		Wu, Ching-Yuan	☒
34	☐	☐	☐	☐	US 6746918 B2	20040608	26	Methods of fabbricating a stack-gate non-volati	438/257	257/314; 438/201;		Wu, Ching-Yuan	☒
35	☐	☐	☐	☐	US 6734055 B1	20040511	13	Multi-level (4 state/2-bit) stacked ga	438/201	438/211; 438/258;		Lin, Chrong Jung et al.	☒
36	☐	☐	☐	☐	US 6720219 B2	20040413	9	Split gate flash memory and formation method th	438/264	438/257; 438/259;		Huang, Tsai-Yu	☒
37	☐	☐	☐	☐	US 6716703 B2	20040406	21	Method of making semiconductor memory de	438/264	438/267; 438/596		Hashimoto, Hiroshi	☒
38	☐	☐	☐	☐	US 6690058 B2	20040210	23	Self-aligned multi-bit flash memory cell and i	257/316	257/390; 257/401;		Wu, Ching-Yuan	☒
39	☐	☐	☐	☐	US 6689658 B2	20040210	24	Methods of fabricating a stack-gate flash memo	438/257	257/315; 257/321;		Wu, Ching-Yuan	☒
40	☐	☐	☐	☐	US 6653188 B1	20031125	9	Method of forming poly tip of floating gate in	438/257	257/E21.20 9;		Huang, Yung-Meng et al.	☒
41	☐	☐	☐	☐	US 6570213	20030527	22	Self-aligned split-gate	257/315	257/314;		Wu, Ching-Yuan	☒